Silicon NPN Power Transistors 2N6260

DESCRIPTION

·With TO-66 package
·Low saturation voltage
·Wide safe operating area

APPLICATIONS

·Power switching circuits
·High-fidelity amplifers
·Solenoid drivers
·Series and shunt-regulator driver and output stages

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	50	V
V_{CEO}	Collector-emitter voltage	Open base	40	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		4	A
I_B	Base current		2	A
P_T	Total power dissipation	T_C=25□	29	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	3.5	□/W

Silicon NPN Power Transistors 2N6260

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1 A ; I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1.5A; I_B=0.15A			1.5	V
V_{BE}	Base -emitter on voltage	I_C=1.5A ; V_{CE}=2V			1.5	V
I_{CEV}	Collector cut-off current	V_{CE}=40V;$V_{BE(off)}$=-1.5V T_C=150□			0.5 1.0	mA
I_{CEO}	Collector cut-off current	V_{CE}=30V; I_B=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			0.2	mA
h_{FE-1}	DC current gain	I_C=4A ; V_{CE}=2V	5			
h_{FE-2}	DC current gain	I_C=1.5A ; V_{CE}=2V	20		100	

PACKAGE OUTLINE

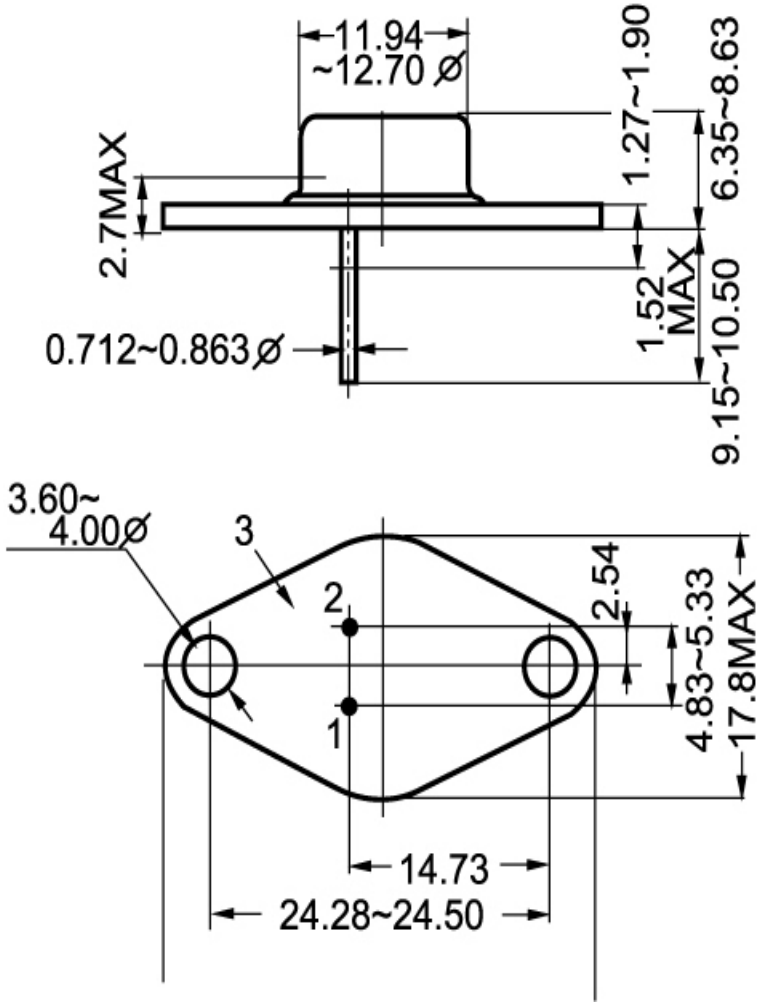

Fig.2 Outline dimensions